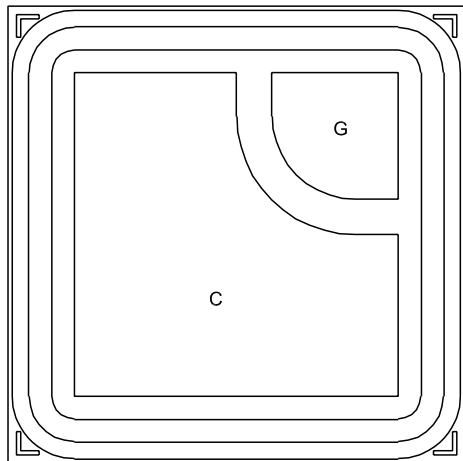


PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	110 x 110 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	80 x 40 MILS
Gate Bonding Pad Area	31 x 31 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



BACKSIDE ANODE R0

GROSS DIER PER 4 INCH WAFER

876

PRINCIPAL DEVICE TYPES

CS220-12M Series
CSDD-12M Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R0 (4- January 2006)